NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI VMB100-12** is Designed for

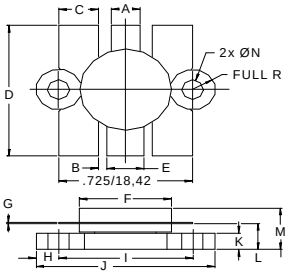
FEATURES:

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- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	20 A
V_{CBO}	36 V
V_{CEO}	18 V
V_{EBO}	4.0 V
P_{DISS}	270 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
θ_{JC}	0.65 ^{O}C/W

PACKAGE STYLE .500 6L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.150 / 3.43	.160 / 4.06
B	.045 / 1.14	
C	.210 / 5.33	.220 / 5.59
D	.835 / 21.21	.865 / 21.97
E	.200 / 5.08	.210 / 5.33
F	.490 / 12.45	.510 / 12.95
G	.003 / 0.08	.007 / 0.18
H	.125 / 3.18	
I	.725 / 18.42	
J	.970 / 24.64	.980 / 24.89
K	.090 / 2.29	.105 / 2.67
L	.150 / 3.81	.170 / 4.32
M		.285 / 7.24
N	.120 / 3.05	.135 / 3.43

ORDER CODE: ASI10747

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 50 mA	36			V
BV_{CES}	I_C = 100 mA	36			V
BV_{CEO}	I_C = 100 mA	18			V
BV_{EBO}	I_E = 10 mA	4.0			V
I_{CES}	V_{CE} = 15 V			15	mA
h_{FE}	V_{CE} = 5.0 V I_C = 5.0 A	20		---	---
C_{OB}	V_{CB} = 12.5 V f = 1.0 MHz			400	pF
P_G	V_{CE} = 12.5 V P_{OUT} = 100 W f = 88 MHz	10			dB
η_C			60		%

Specifications are subject to change without notice.